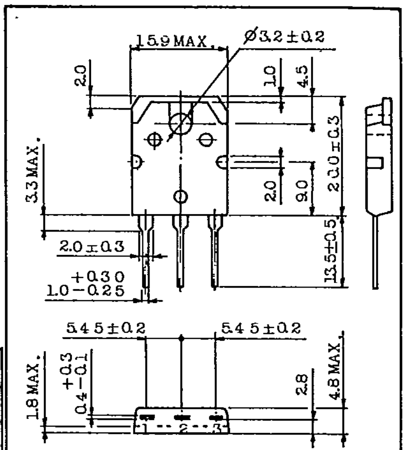
SILICON NPN TRIPLE DIFFUSED TYPE

2SC3182

POWER AMPLIFIER APPLICATIONS.

Unit in mm



1. BASE
2. COLLECTOR (HEAT SINK)
3. EMITTER

JEDEC	—
EIAJ	—
TOSHIBA	2-16B1A

Weight : 4.6g

FEATURES:

- Complementary to 2SA1265
- Recommend for 70W High Fidelity Audio Frequency Amplifier Output Stage

MAXIMUM RATINGS ($Ta=25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	140	V
Collector-Emitter Voltage	V_{CEO}	140	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	10	A
Base Current	I_B	1	A
Collector Power Dissipation ($Tc=25^{\circ}C$)	P_C	100	W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55~150	$^{\circ}C$

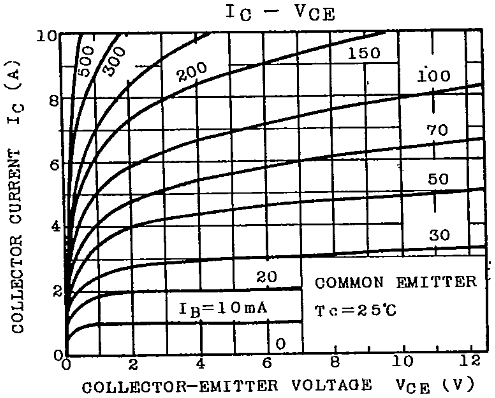
ELECTRICAL CHARACTERISTICS ($Ta=25^{\circ}C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=140V,\ I_E=0$	-	-	5.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V,\ I_C=0$	-	-	5.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=50mA,\ I_B=0$	140	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=5V,\ I_C=1A$	55	-	160	
	$h_{FE(2)}$	$V_{CE}=5V,\ I_C=5A$	35	83	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=7A,\ I_B=0.7A$	-	0.3	2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=5V,\ I_C=5A$	-	0.9	1.5	V
Transition Frequency	f_T	$V_{CE}=5V,\ I_C=1A$	-	30	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V,\ I_E=0,\ f=1MHz$	-	220	-	pF

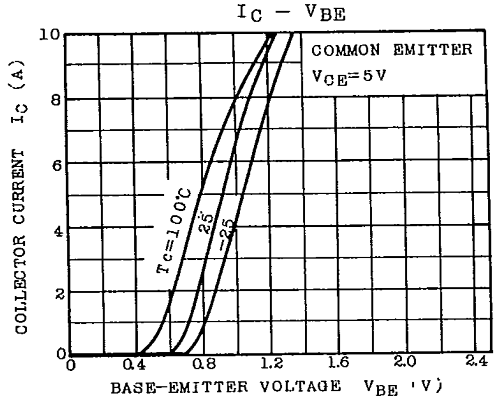
Note : $h_{FE(1)}$ Classification R : 55~110, O : 80~160

2SC3182

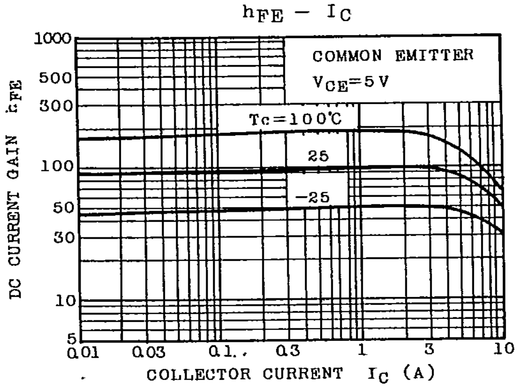
$I_C - V_{CE}$



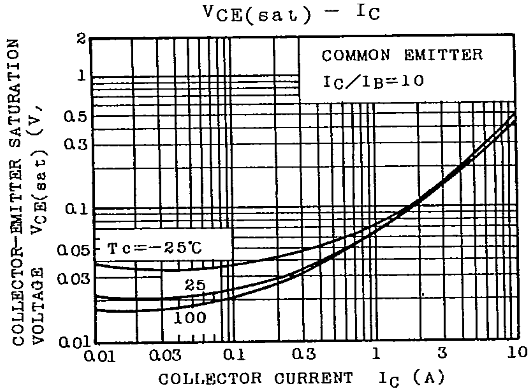
$I_C - V_{BE}$



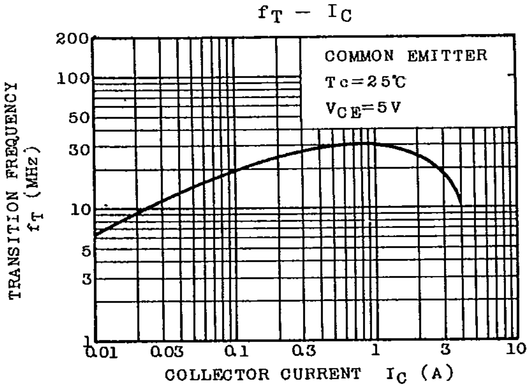
$h_{FE} - I_C$



$V_{CE(sat)} - I_C$



$f_T - I_C$



SAFE OPERATING AREA

